Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L6	2521	(257/773).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/12 10:07
L7	44	L6 and heat with interconnect\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L8	107	("3539705" "3846166" "4096623" "4164461" "4308090" "4601915" "4670091" "4849070").PN. OR ("5117276").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:07
L9	12	("5117276" "5444015" "5798559" "6245658" "6255712" "6277728" "6386939" "6403461" "6614092").PN. OR ("6713835"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:07
L10	1470	L6 and line	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L11	382	L6 and line with (power signal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L12	9	("5814844" "5874754" "6091088" "6114767" "6133079" "6177709" "6288447" "6320234" "6326651").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:07
L13	10	dummy near interconnection with heat	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:07
L14	7	("5441915" "5729047" "5811352").PN. OR ("6717267"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:07
L15	10	dummy near interconnection same heat	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:07
L16	11	dummy near interconnection same heat .	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/05/12 10:07

L17	1	L16 not L15	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/05/12 10:07
L18	41	dummy near interconnection and heat	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/05/12 10:07
L19	4	(US-20020058411-\$).did. or (US-6800883-\$ or US-6717267-\$ or US-6913990-\$ or US-6664642-\$). did.	US-PGPUB; USPAT	OR	ON	2006/05/12 10:07
L20	53	interconnection with heat adj transfer and (IC integrated adj circuit chip die wafer semiconductor silicon).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L21	677	(via damascene) with heat adj transfer and (IC integrated adj circuit chip die wafer semiconductor silicon).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L22	10	(damascene) with heat adj transfer and (IC integrated adj circuit chip die wafer semiconductor silicon).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L23	4	(via near4 dummy) with heat adj transfer and (IC integrated adj circuit chip die wafer semiconductor silicon).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L24	0	(interconnect near4 dummy) with heat adj transfer and (IC integrated adj circuit chip die wafer semiconductor silicon).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L25	0	(interconnect near4 dummy) with heat adj transf\$3 and (IC integrated adj circuit chip die wafer semiconductor silicon).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07

L26	0	(interconect near4 dummy) with heat adj transf\$3 and (IC integrated adj circuit chip die wafer semiconductor silicon).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L27		(interconnecting near4 dummy) with heat adj transf\$3 and (IC integrated adj circuit chip die wafer semiconductor silicon).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L28	0	(pattern near4 dummy) with heat adj transf\$3 and (IC integrated adj circuit chip die wafer semiconductor silicon).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L29	0	(pattern near4 dummy) with heat adj transf\$4 and (IC integrated adj circuit chip die wafer semiconductor silicon).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L30	13	(pattern near4 dummy) with heat near2 (transfer\$3 dissipat\$3)and (IC integrated adj circuit chip die wafer semiconductor silicon).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L31	13	(dummy near4 pattern) with heat near2 (transfer\$3 dissipat\$3)and (IC integrated adj circuit chip die wafer semiconductor silicon).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L32	1	(dummy near interconnect\$3) with heat near2 (transfer\$3 dissipat\$3)and (IC integrated adj circuit chip die wafer semiconductor silicon).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L33	3	(dummy near interconnect\$3) with heat near2 (transfer\$3 dissipat\$3)and (IC integrated adj circuit chip die wafer semiconductor silicon). clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L34	416	epoxy with phenolic with curing adj accelerator with inorganic adj filler	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07

L35	82170	heat with dissipation	US-PGPUB; USPAT; USOCR;	OR	ON	2006/05/12 10:07
			EPO; JPO; DERWENT; IBM_TDB			
L36	4382747	(semiconductor ic integrated adj circuit die chip wafer silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L37	178540	power near2 line	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L38	237	interconnect with L35	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L39	206	L38 and L36	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L40	16	L39 and L37	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L41	5919	heat with interconnect	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L42	2880	L41 and L36	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L43	160	L42 and L37	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07

L44	220442	heat with (wir\$3 via damascene trench)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L45	75495	L44 and L36	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L46	4518	L44 with L35	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L47	2640	L46 and L36	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L48	109	L47 and L37	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L49	35	L48 and "257"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L50	57194	(257/7\$2).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/12 10:07
L51	8828	(257/69\$1).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/12 10:07
L52	61660	L50 L51	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07

L53	10871	L52 and heat with (dissipat\$3 remov\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L54	9419	L52 and heat near2 (dissipat\$3 remov\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L55	5572111	L54 and heat (interconnection via plug wir\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L56	427180	heat with (dissipat\$3 remov\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L57	5569633	(interconnection via plug wir\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L58	25883	L56 with L57	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L59	1866	L52 and L58	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB	OR	ON	2006/05/12 10:07
L60	243371	heat near2 (dissipat\$3 remov\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L61	14701	L60 with L57	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07

L62	1497	L61 and L50	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L63	958	L61 and L50	USPAT	OR	ON	2006/05/12 10:07
L64	2520	(257/774).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/12 10:07
L65	48	L61 and L64	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L66	3732	(257/758).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/12 10:07
L67	34	L61 and L66	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L68	5	("5698897" "5792677").PN. OR ("6242807").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:07
L69	876	(257/760).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/12 10:07
L70	4	L61 and L69	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L71	372	(257/761).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/12 10:07

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L72	4	L61 and L70	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L73	5239	(257/76\$1).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/12 10:07
L74	19	L61 and L73	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L75	9	("5700735" "5736791" "5739587" "5891799" "5923088" "6028367" "6143396" "6180511" "6251781") PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:07
L76	6	("6028367").URPN.	USPAT	OR	ON	2006/05/12 10:07
L77	12	("5248903" "5404047" "5736791" "5739587" "5923088" "5959356").PN. OR ("6028367"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:07
L78	12	("5248903" "5404047" "5736791" "5739587" "5923088" "5959356").PN. OR ("6028367"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:07
L79	3	("5354717" "6018193" "20020061614").pn.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:07
L80	2	L79 and heat	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:07
L81	1	"6717267".pn. and power	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:07
L82	504	double with heat with sink	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:07
L83	205	L82 and "257"/\$.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:07
L84	148	L82 and "257"/\$.ccls.	USPAT	OR	ON	2006/05/12 10:07
L85	58	L84 and wire	USPAT	OR	ON	2006/05/12 10:07
L86	144	andujar.xa.	USPAT	OR	ON	2006/05/12 10:07
L87	0	aluminum near2 thermal with expasion with epoxy	USPAT	OR	ON	2006/05/12 10:07

L88	0	aluminum near2 thermal with expasion	USPAT	OR	ON	2006/05/12 10:07
L89	4737	aluminum near2 thermal	USPAT	OR	ON	2006/05/12 10:07
L90	221	(wir\$2 with interconnection) with copper	USPAT	OR	ON	2006/05/12 10:07
L91	2	"6717267".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L92	2	"6,600,175".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L93	0	L92 and power with 25b	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L94	0	L92 and power same 25b	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L95	0	L92 and 25b	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L96	0	L91 and power with 25b	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L97	1	L91 and power same 25b	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L98	2	"5177594".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07

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L99	1357	siN with metallic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L100	124	siN near2 metallic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L101	3313	substrate with pin with board	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L102	241	substrate with pin with direct\$4 with board	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L103	65	L102 and "257"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L104	9	("20020011662" "20020074653" "20020185308" "5939782" "6353540" "6400576" "6518666" "6535398" "6727780").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:07
L105	20	("4322778" "4574255" "4755910" "4811082" "4901136" "5014114" "5032896" "5075253" "5077639" "5095402" "5177670" "5237204" "5239198" "5239448" "5255431" "5384691" "5473513" "6018463" "6147876" "6153290").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:07
L106	119	("4064552" "4081898" "4104728" "4177519" "4495546" "4567543" "4598337" "4672152" "4744008" "4754371" "4843520" "4926241" "4933810" "4937707" "4967950" "4982376" "4987100" "4990948" "5028983").PN. OR ("5239448"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:07
L107	11	("4612083" "4939568" "5138437" "5191405" "5202754" "5239448" "5266511" "5380681" "5489554" "5579207").PN. OR ("6593645"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:07

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L108	2521	(257/773).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/12 10:07
L109	1470	L108 and line	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L110	10	dummy near interconnection same heat	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:07
L111	11	dummy near interconnection same heat	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/05/12 10:07
L112	41	dummy near interconnection and heat	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/05/12 10:07
L113	677	(via damascene) with heat adj transfer and (IC integrated adj circuit chip die wafer semiconductor silicon).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L114	0	(interconnect near4 dummy) with heat adj transfer and (IC integrated adj circuit chip die wafer semiconductor silicon).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L115	0	(interconnect near4 dummy) with heat adj transf\$3 and (IC integrated adj circuit chip die wafer semiconductor silicon).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:07
L116	0	(interconect near4 dummy) with heat adj transf\$3 and (IC integrated adj circuit chip die wafer semiconductor silicon).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L117	0	(interconnecting near4 dummy) with heat adj transf\$3 and (IC integrated adj circuit chip die wafer semiconductor silicon).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08

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L118	0	(pattern near4 dummy) with heat adj transf\$3 and (IC integrated adj circuit chip die wafer semiconductor silicon).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L119	0	(pattern near4 dummy) with heat adj transf\$4 and (IC integrated adj circuit chip die wafer semiconductor silicon).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L120	13	(dummy near4 pattern) with heat near2 (transfer\$3 dissipat\$3)and (IC integrated adj circuit chip die wafer semiconductor silicon).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L121	1	(dummy near interconnect\$3) with heat near2 (transfer\$3 dissipat\$3) and (IC integrated adj circuit chip die wafer semiconductor silicon).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L122	416	epoxy with phenolic with curing adj accelerator with inorganic adj filler	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L123	82170	heat with dissipation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L124	4382747	(semiconductor ic integrated adj circuit die chip wafer silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L125	178540	power near2 line	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L126	237	interconnect with L123	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08

L127	206	L126 and L124	US-PGPUB; USPAT;	OR	ON	2006/05/12 10:08
			USOCR; EPO; JPO; DERWENT; IBM_TDB			
L128	5919	heat with interconnect	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L129	2880	L128 and L124	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L130	220442	heat with (wir\$3 via damascene trench)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L131	75495	L130 and L124	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L132	4518	L130 with L123	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L133	2640	L132 and L124	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L134	57194	(257/7\$2).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/12 10:08
L135	8828	(257/69\$1).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/12 10:08

L136	61660	L134 L135	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L137	10871	L136 and heat with (dissipat\$3 remov\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L138	9419	L136 and heat near2 (dissipat\$3 remov\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L139	5572111	L138 and heat (interconnection via plug wir\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L140	427180	heat with (dissipat\$3 remov\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L141	5569633	(interconnection via plug wir\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L142	25883	L140 with L141	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L143	1866	L136 and L142	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L144	243371	heat near2 (dissipat\$3 remov\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08

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L145	14701	L144 with L141	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L146	1497	L145 and L134	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L147	2520	(257/774).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/12 10:08
L148	3732	(257/758).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/12 10:08
L149	876	(257/760).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/12 10:08
L150	372	(257/761).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/12 10:08
L151	5239	(257/76\$1).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/12 10:08
L152	6	("6028367").URPN.	USPAT	OR	ON	2006/05/12 10:08
L153	12	("5248903" "5404047" "5736791" "5739587" "5923088" "5959356").PN. OR ("6028367"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:08
L154	504	double with heat with sink	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:08
L155	0	aluminum near2 thermal with expasion with epoxy	USPAT	OR	ON	2006/05/12 10:08
L156	0	aluminum near2 thermal with expasion	USPAT	OR	ON	2006/05/12 10:08

L157	4737	aluminum near2 thermal	USPAT	OR	ON	2006/05/12 10:08
L158	221	(wir\$2 with interconnection) with copper	USPAT	OR	ON	2006/05/12 10:08
L159	1	L111 not L110	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/05/12 10:08
L160	1	"6717267".pn. and power	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:08
L161	44	L108 and heat with interconnect\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L162	12	("5117276" "5444015" "5798559" "6245658" "6255712" "6277728" "6386939" "6403461" "6614092").PN. OR ("6713835"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:08
L163	9	("5814844" "5874754" "6091088" "6114767" "6133079" "6177709" "6288447" "6320234" "6326651").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:08
L164	10	dummy near interconnection with heat	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:08
L165	7	("5441915" "5729047" "5811352").PN. OR ("6717267"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:08
L166	4	(US-20020058411-\$).did. or (US-6800883-\$ or US-6717267-\$ or US-6913990-\$ or US-6664642-\$). did.	US-PGPUB; USPAT	OR	ON	2006/05/12 10:08
L167	53	interconnection with heat adj transfer and (IC integrated adj circuit chip die wafer semiconductor silicon).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L168	10	(damascene) with heat adj transfer and (IC integrated adj circuit chip die wafer semiconductor silicon).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08

L169	4	(via near4 dummy) with heat adj transfer and (IC integrated adj circuit chip die wafer semiconductor silicon).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L170	13	(pattern near4 dummy) with heat near2 (transfer\$3 dissipat\$3)and (IC integrated adj circuit chip die wafer semiconductor silicon).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L171	3	(dummy near interconnect\$3) with heat near2 (transfer\$3 dissipat\$3) and (IC integrated adj circuit chip die wafer semiconductor silicon). clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L172	16	L127 and L125	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L173	109	L133 and L125	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L174	35	L173 and "257"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L175	48	L145 and L147	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L176	34	L145 and L148	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L177	5	("5698897" "5792677").PN. OR ("6242807").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:08

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L178	4	L145 and L149	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L179	4	L145 and L178	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L180	19	L145 and L151	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L181	9	("5700735" "5736791" "5739587" "5891799" "5923088" "6028367" "6143396" "6180511" "6251781").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:08
L182	12	("5248903" "5404047" "5736791" "5739587" "5923088" "5959356").PN. OR ("6028367"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:08
L183	3	("5354717" "6018193" "20020061614").pn.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:08
L184	2	L183 and heat	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:08
L185	148	L154 and "257"/\$.ccls.	USPAT	OR	ON	2006/05/12 10:08
L186	58	L185 and wire	USPAT	OR	ON	2006/05/12 10:08
L187	107	("3539705" "3846166" "4096623" "4164461" "4308090" "4601915" "4670091" "4849070").PN. OR ("5117276").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:08
L188	160	L129 and L125	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L189	109	L133 and L125	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L190	205	L154 and "257"/\$.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/12 10:08

L191	148	L154 and "257"/\$.ccls.	USPAT	OR	ON	2006/05/12 10:08
L192	144	andujar.xa.	USPAT	OR	ON	2006/05/12 10:08
L193	382	L108 and line with (power signal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/12 10:08
L194	958	L145 and L134	USPAT	OR	ON	2006/05/12 10:08